

Description

The CR range of protectors are based on the proven technology of the T10 thyristor product. Designed for transient voltage protection of telecommunications equipment, it provides higher power handling than a conventional avalanche diode (TVS) and when compared to a GDT offers lower voltage clamping levels and infinite surge life.

Packaged in a transfer molded DO-214AA surface mount outline designed for high speed pick & place machines used in today's surface mount assembly lines.

Electrical Characteristics

The electrical characteristics of a CRXXXX device is similar to that of a self gated Triac, but the CR is a two terminal device with no gate. The gate function is achieved by an internal current controlled mechanism.

Like the T.T.S. diodes, the CRXXXX has a standoff voltage (V_{RM}) which should be equal to or greater than the operating voltage of the system to be protected. At this voltage (V_{RM}) the current consumption of the CRXXXX is negligible and will not effect the protected system.

When a transient occurs, the voltage across the CRXXXX will increase until the breakdown voltage (V_{BR}) is reached. At this point the device will operate in a similar way to a T.V.S. device and is in an avalanche mode.

The voltage of the transient will now be limited and will only increase by a few volts as the device diverts more current. As this transient current rises, a level of current through the device is reached (I_{BO}) which causes the device to switch to a fully conductive state such that the voltage across the device is now only a few volts (V_T). The voltage at which the device switches from the avalanche mode to the fully conductive state (V_T) is known as the Breakover Voltage (V_{BO}). When the device is in the V_T state, high currents can be diverted without damage to the CRXXXX due to the low voltage across the device, since the limiting factor in such

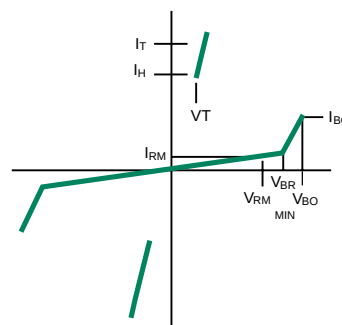
devices is dissipated power ($V \times I$).

Resetting of the device to the non conducting state is controlled by the current flowing through the device. When the current falls below a certain value, known as the Holding Current (I_H), the device resets automatically.

As with the avalanche T.V.S. device, if the CRXXXX is subjected to a surge current which is beyond its maximum rating, then the device will fail in short circuit mode, this ensures that the equipment is ultimately protected.

Selecting A CRXXXX

1. When selecting a CRXXXX device, it is important that the V_{RM} of the device is equal to or greater than the operating voltage of the system.
2. The minimum Holding Current (I_H) must be greater than the current the system is capable of delivering otherwise the device will remain conducting following a transient condition.



*V-I Graph
Illustrating Symbols
and Terms for
the CR Surge
Protection Device.*

The CRXXXX Range Can Be Used to Protect Against Surges As Defined In The Following International Standards.

			SA	SB	SC
FCC Rules Part 68/D	Metallic Longitudinal	10/560μs 10/160μs	50A 100A	100A 150A	100A 200A
Bellcore Specification	TR-NWT-001089	10/1000μs 2/10μs 100v/μs	37A - 1KV	75A - 1KV	100A 500A 1KV
ITU K-17 (Formerly CCITT)	Voltage Wave Form Current Wave Form	100/700μs 5/310μs	- -	1.5KV 38A	1.5KV 38A
VDE 0433	Voltage Wave Form Current Wave Form	10/700μs 5/310μs	- -	2KV 50A	4.0KV 100A
C-NET 131-24	Voltage Wave From Current Wave Form	0.5/700μs 0.8/310μs	1.0KV 25A	1.0KV 25A	4.0KV 100A
IEC 1000-4-5	(Discharge through 2Ω impedance) I Voltage Wave Form	8/20μs 1-2/50μs	- -	100A 300V	250A 500V
ITU K-20 (Formerly CCITT)	Voltage Wave Form Current Wave Form	10/700μs 5/310μs	1000V 25A	10000V 25A	4000V 100A

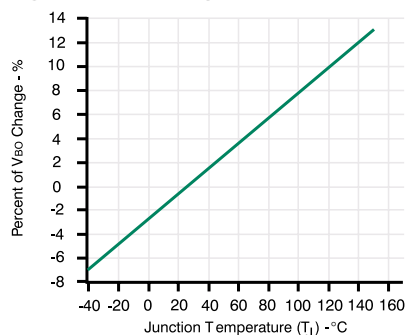
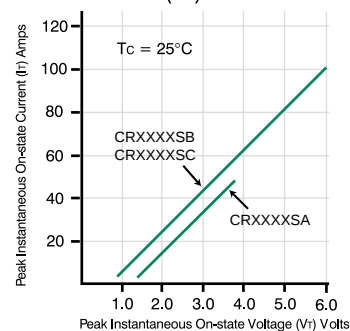
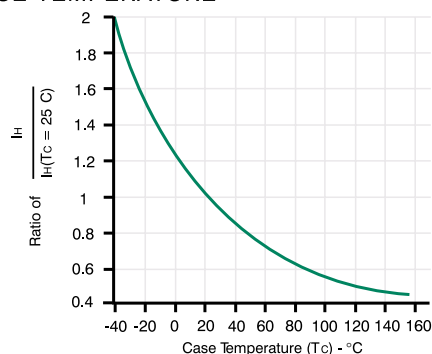
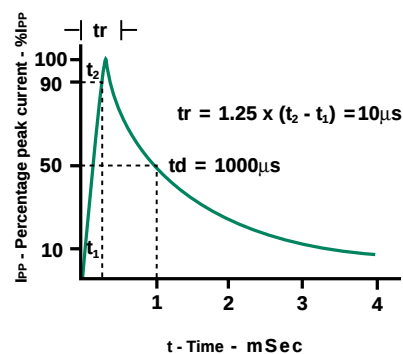
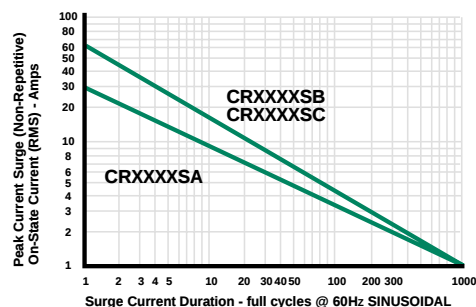
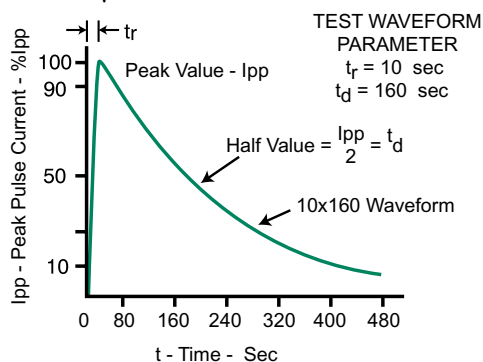
Specifications

Electrical Charecteristics (Tj=25°C)

SYMBOL	PARAMETER	SYMBOL	PARAMETER
V _{RM}	Stand-off Coltage	I _{RM}	Stand-off Current
V _{BR}	Breakdown Voltage	I _{BO}	Breakover Current
V _{BO}	Breakover Voltage	I _H	Holding Current
V _T	On-State Voltage		

THERMAL DATA		VALUE	UNIT
T _{stg}	Storage and Operating Junction Temperature range	-40 to +150	°C
T _j		150	°C
TL	Maximum Temperature For Soldering (For period of 10 seconds max)	230	°C

	Stock Number	Device Code	Reverse Stand-off Voltage	Maximum Reverse Leakage μ A	Maximum Breakover Voltage @I _{BO}	Maximum Breakover Current mA	Minimum Holding Current mA	Maximum On-State Voltage @1A	Typical Capacitance @1MHz 2v bias pF
MAXIMUM RATINGS		CR 0300 SA	25	5	40	800	150	5	100
SUFFIX SA		CR 0640 SA	58	5	77	800	150	5	60
		CR 0720 SA	65	5	88	800	150	5	60
I _{pp} 10x160 μ s Amps 100		CR 0800 SA	75	5	98	800	150	5	60
I _{pp} 10x560 μ s Amps 50		CR 1100 SA	90	5	130	800	150	5	60
I _{TSM} 60Hz Amps 20		CR 1300 SA	120	5	160	800	150	5	40
DI/dt Amps/ μ s 500		CR 1500 SA	140	5	180	800	150	5	40
		CR 1800 SA	160	5	220	800	150	5	40
MAXIMUM RATINGS		CR 2300 SA	190	5	260	800	150	5	30
SUFFIX SB		CR 2600 SA	220	5	300	800	150	5	30
I _{pp} 10x160 μ s Amps 150		CR 3100 SA	275	5	350	800	150	5	30
I _{pp} 10x560 μ s Amps 100		CR 3500 SA	320	5	400	800	150	5	30
I _{TSM} 60Hz Amps 30		CR 0300 SB	25	5	40	800	150	5	100
DI/dt Amps/ μ s 500		CR 0640 SB	58	5	77	800	150	5	60
		CR 0720 SB	65	5	88	800	150	5	60
		CR 0800 SB	75	5	98	800	150	5	60
		CR 1100 SB	90	5	130	800	150	5	60
		CR 1300 SB	120	5	160	800	150	5	40
		CR 1500 SB	140	5	180	800	150	5	40
		CR 1800 SB	160	5	220	800	150	5	40
		CR 2300 SB	190	5	260	800	150	5	30
		CR 2600 SB	220	5	300	800	150	5	30
		CR 3100 SB	275	5	350	800	150	5	30
		CR 3500 SB	320	5	400	800	150	5	30
MAXIMUM RATINGS		CR 0300 SC	25	5	40	800	150	5	200
SUFFIX SC		CR 0640 SC	58	5	77	800	150	5	120
I _{pp} 2x10 μ s Amps 500		CR 0720 SC	65	5	88	800	150	5	120
I _{pp} 10x160 μ s Amps 200		CR 0800 SC	75	5	98	800	150	5	120
I _{pp} 10x560 μ s Amps 100		CR 1100 SC	90	5	130	800	150	5	120
I _{TSM} 60Hz Amps 60		CR 1300 SC	120	5	160	800	150	5	80
di/dt Amps/ μ s 500		CR 1500 SC	140	5	180	800	150	5	80
		CR 1800 SC	160	5	220	800	150	5	80
		CR 2300 SC	190	5	260	800	150	5	60
		CR 2600 SC	220	5	300	800	150	5	60
		CR 3100 SC	275	5	350	800	150	5	60
		CR 3500 SC	320	5	400	800	150	5	60

TYPICAL V_{BO} CHANGE vs JUNCTION TEMPERATURE

ON-STATE VOLTAGE (V_T) vs ON-STATE CURRENT (I_T)

TYPICAL DC HOLDING CURRENT vs CASE TEMPERATURE

PULSE WAVE FORM (10/10000 μ S)

PEAK SURGE ON-STATE CURRENT VS. SURGE CURRENT DURATION

10x160 μ S PULSE WAVE FORM

10x560 μ S PULSE WAVE FORM
